

MEMS Nanopositioning Mechanisms: Design and Experimental Characterization

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Outline

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 - NIST macro-scale nanopositioners
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 - 1 DOF and 2 DOF mechanisms
- Mechanism Characterization
 - Methodology: SEM and OM
 - Displacement voltage calibration
 - Cross-talk error and rotational error measurements
- Conclusion

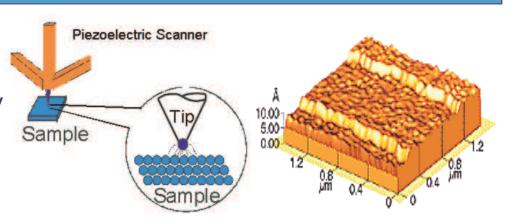




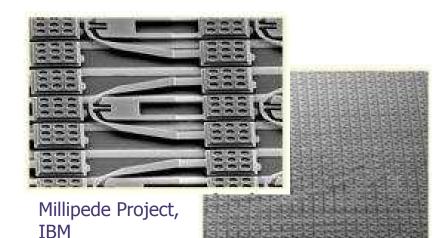
MEMS Nanopositioning

Nanopositioner Applications:

- Atomic Force Microscopy
- Scanning Tunneling Microscopy
- Optical Tweezers
- Nanomanipulation
- Beam Steering



MEMS Nanopositioners:



Applications:

- High-density data storage (IBM, Nanochip, etc.)
- Scanning probe arrays
- Parallel nanomanipulation and assembly
- Beam steering (alternative to micromirrors)

Critical Issues:

- Matching precision of macro-scale devices
- Controlling large arrays of MEMS
- Structural robustness, redundancy, failure

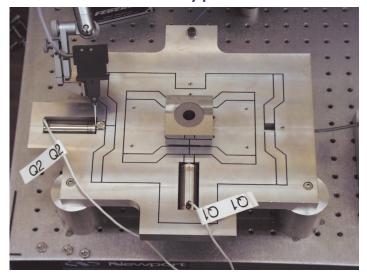




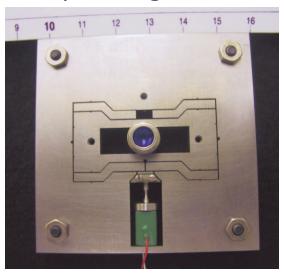
Parallel Dual Lever Nanopositioners

A number of novel macro-scale nanopositioning devices, which combine flexure mechanisms with piezoelectric actuators, have been developed at NIST.

First Prototype: 2 DOF



Compact Stages: 1 and 2 DOF mechanisms



Dimensions: ~ 8 X 8 cm

Materials:

Aluminum

Beryllium Copper

Invar

Steel

Titanium Alloy

Range: ~ 100 μm

- The parallel dual lever flexure mechanism uses symmetry for high precision guided motion
- Cross-talk and rotational motion errors have been shown to be very small





Design Objectives and Specifications

Project Objectives:

- Develop devices which meet or exceed the specifications of our macro-scale nanopositioners (range, resolution, accuracy, bandwidth, etc.)
- Apply these devices to critical problems in nanometrology (AFM, STM) and nanomanufacturing (nanoassembly)

Device Specifications:

- Motion range ~ > 20 μm
- Motion resolution ~ 5 nm
- Positioning accuracy ~ < 50 nm
- Cross-talk error ~ < 250 nm
- Rotational errors ~ < 10 μrad
- System Bandwidth ~ > 1 kHz

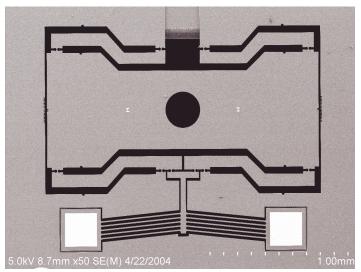
Design Considerations:

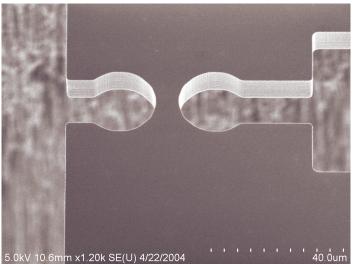
- Mechanisms must be strong enough for the connection of probes, grippers, etc.
- Scalable design, 1 DOF, 2 DOF, etc.

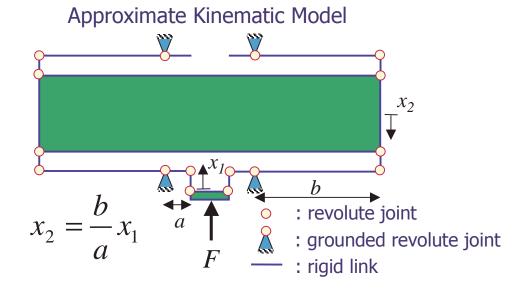




Mechanism Kinematics







- Circular notch flexure hinges are used for compliance (5 μm thickness)
- The flexures act as torsional springs or combined torsion/shear springs, depending on their location
- The motion amplification can easily be adjusted for different applications





Electro-Thermal Actuation

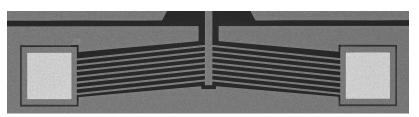
Bent-beam, or 'chevron', electro-thermal actuators have been selected for the

nanopositioners due to their:

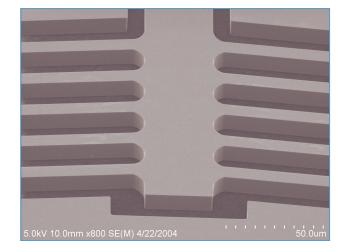
- Straight line motion
- High force output
- Low voltage requirements
- Simple design and fabrication

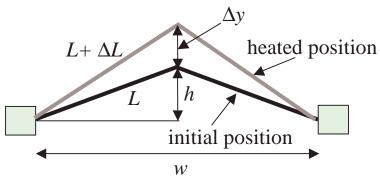
Working Principle:

Voltage applied across the structure causes Joule heating, resulting in an expansion of the beams and linear motion of the transmission shuttle



$$\Delta y = \left((L + \Delta L)^2 + \frac{1}{4} w^2 \right)^{\frac{1}{2}} - h$$



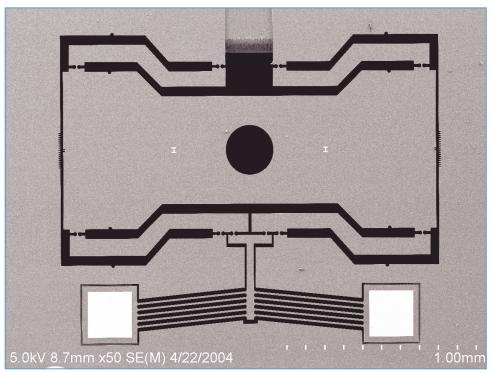


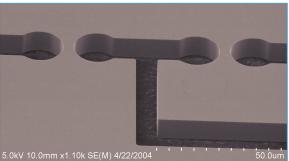
$$\Delta L = \alpha L \Delta T$$





1 DOF Mechanism





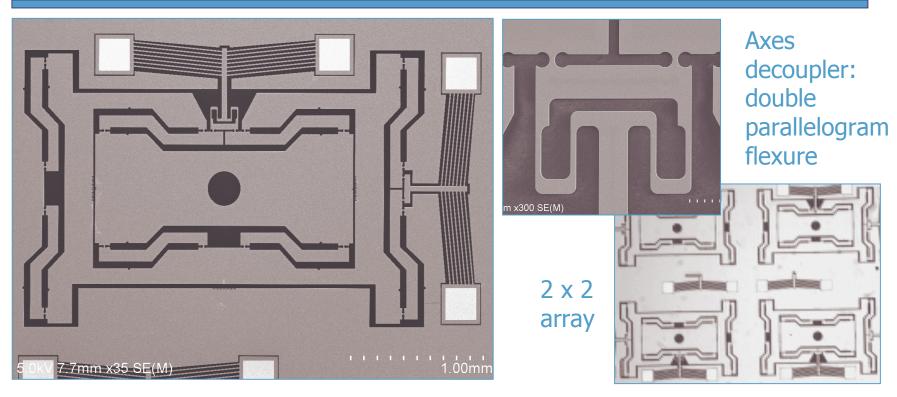
The 1 DOF mechanism incorporates a dual lever flexure mechanism with a bent-beam electro-thermal actuator

- This mechanism is large in comparison to most MEMS (2 mm x 2 mm) due to structural constraints
- Range $\sim 15 \, \mu \text{m}$
- Device layer thickness = 10 μ m and 25 μ m
- Flexure width = $5 \mu m$ and $7 \mu m$
- Input voltage ~ 0 V to 15 V
- The bandwidth has not been measured yet, but it is expected to be limited by the thermal actuator rather than structural modes





2 DOF Mechanism



- The 2 DOF mechanism cannot use the nested design utilized in our macroscale nanopositioners due to constraints on the actuator fabrication
- Therefore, a coupled design has been adopted and a decoupling actuator transmission has been added.
- A prototype nanopositioner array has been fabricated

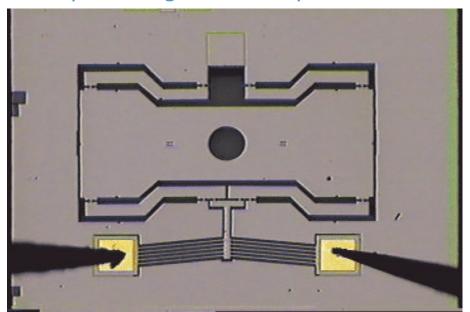




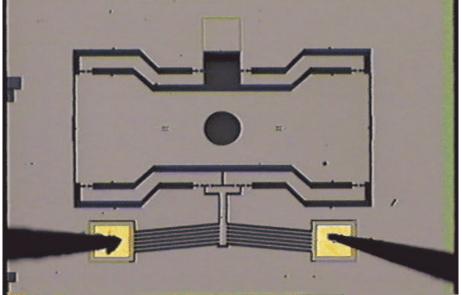
Mechanism Operation

Initial tests performed on a probing station and captured with a standard optical microscope and video camera

Input voltage = 1 Hz square wave



Input voltage = 3 Hz sine wave







Performance Characterization Methodology

Needs

- The mechanisms currently do not have built-in displacement sensors
- Standard sensors will need a calibration approach with the desired resolution (~ 5 nm)
- Several possible metrology tools already exist, based on white light interferometry, laser interferometry and video microscopy (see Veeco, Polytec, Umech)
- These instruments are very expensive and their results are difficult to verify due to proprietary software
- A scanning electron microscope will provide the same level of precision (or better) as any of these instruments when analyzing static performance

<u>Approach</u>

- Devices were placed in an SEM with a feed-through for providing input voltages
- Input voltages were applied and images were taken successively for the range of interest
- Image processing techniques were applied to extract the motion of the output stage along the y axis (desired linear motion), x axis (cross-talk error), and rotation about the z axis (yaw error)

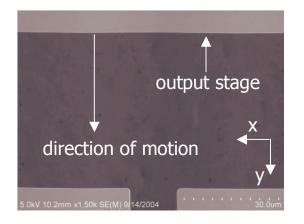




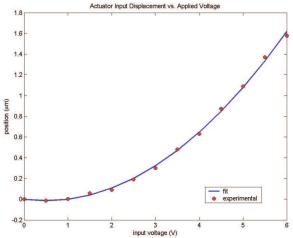
Displacement - Voltage Calibration - SEM

- An SEM is used to take static images of the device 50 nm pixel resolution
- The edge of the output stage is detected and an average vertical position is calculated
- The relative displacement for each voltage increment is calculated, resulting in a displacement - voltage calibration curve
- The data is strongly quadratic, with the second order term providing the largest weight, as would be expected for a thermal actuator ($y \propto V^2$)

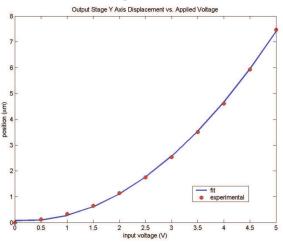
Typical Image



Actuator Motion



Stage Motion



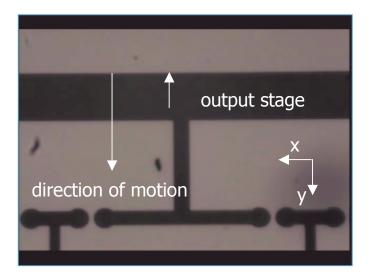




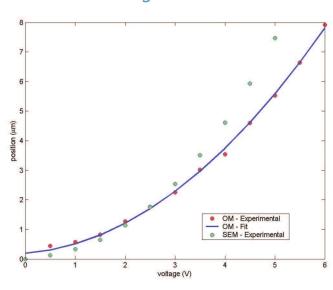
Displacement - Voltage Calibration

- An optical microscope was used to take static images 500 nm pixel resolution
- The displacements were significantly smaller due to the effects of convection in air
- Calibration in air is necessary for many applications (AFM, beam steering)
- Therefore, the relationship between air and vacuum operation needs to be determined

Typical Image



Stage Motion





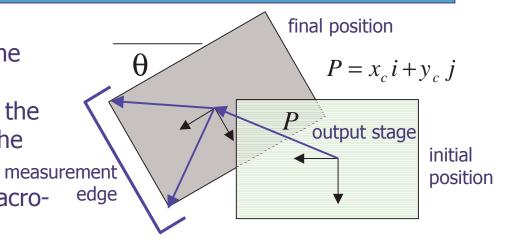


Cross-Talk Error

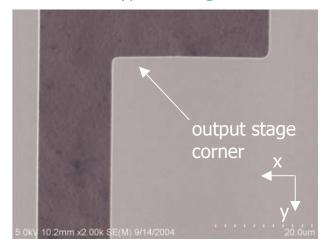
 Cross-talk and rotational errors are coupled when measuring them at the edge of the output stage

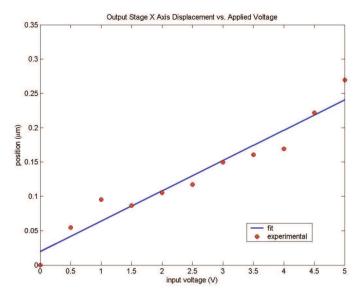
 A simpler metric of the cross-talk is the maximum deviation orthogonal to the desired axis of motion

• The cross-talk is linear, as in the macroscale mechanism $\sim 0.036~\mu\text{m}/~\mu\text{m}$



Typical Image









Rotational Errors

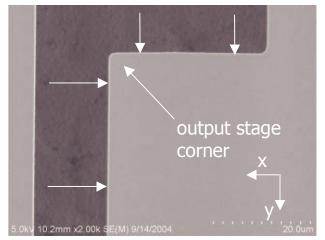
 Two points on the vertical and horizontal edges are measured

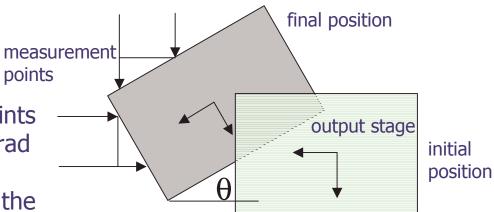
• The rotation is a function of the differential displacement of these points

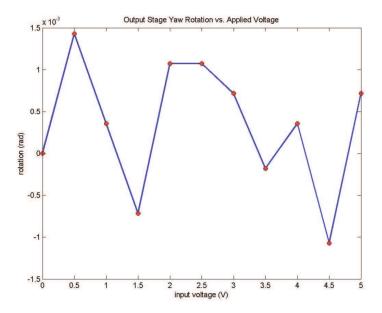
• The error was on the order of 1.5 mrad

 However, the measurements are inconsistent, indicating a problem in the methodology

Typical Image











Conclusion

- MEMS nanopositioners based on a novel flexure mechanism have been designed, fabricated, and put through an initial set of performance tests
- The SEM, coupled with image processing, proved to be a straightforward and precise approach for characterizing the static performance of these devices
- The devices do not currently meet our desired specifications, but these results indicate that the specifications should be obtainable through modification of the design and additional testing

Work in Progress

- Redesign for stiffer stage (less cross-talk, rotation, etc.)
- Calibrated open-loop control (nanometer steps, trajectory following)
- Incorporate sensors (piezoresistive, fiber optic interferometers)
- Dynamic testing, frequency response, dynamic modeling
- Closed-loop control



